



1N5817 - 1N5819

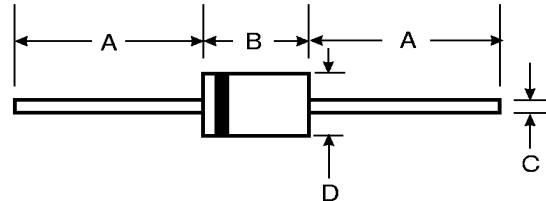
1.0A SCHOTTKY BARRIER RECTIFIER

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Application
- Plastic Material - UL Flammability Classification 94V-0

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.3 grams (approx)
- Mounting Position: Any
- Marking: Type Number



DO-41 Plastic		
Dim	Min	Max
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	1N5817	1N5818	1N5819	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average Rectified Output Current (Note 1) @ $T_L = 90^\circ\text{C}$	I_O	1.0			A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	25			A
Forward Voltage @ $I_F = 1.0\text{A}$ @ $I_F = 3.0\text{A}$	V_{FM}	0.450 0.750	0.550 0.875	0.60 0.90	V
Peak Reverse Leakage Current at Rated DC Blocking Voltage @ $T_A = 25^\circ\text{C}$ @ $T_A = 100^\circ\text{C}$	I_{RM}	1.0 10			mA
Typical Junction Capacitance (Note 2)	C_j	110			pF
Typical Thermal Resistance Junction to Lead (Note 1)	$R_{\theta JL}$	60			K/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150			$^\circ\text{C}$

Notes: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.

